

ABSTRACT OF THE DISCLOSURE

A method of manufacturing a semiconductor device may include forming a fin on an insulator and forming a gate oxide on sides of the fin. The method may also include forming a gate structure over the fin and the gate oxide and forming a dielectric layer adjacent the gate structure. Material in the gate structure may be removed to define a gate recess. A width of a portion of the fin below the gate recess may be reduced, and a metal gate may be formed in the gate recess.